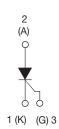


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Vishay Semiconductors

Thyristor High Voltage, Phase Control SCR, 40 A





TO-247AC

PRODUCT SUMMARY							
Package	TO-247AC						
Diode variation	Single SCR						
I _{T(AV)}	35 A						
V _{DRM} /V _{RRM}	800 V, 1200 V						
V_{TM}	1.45 V						
I _{GT}	150 mA						
T _J	-40 °C to +125 °C						

FEATURES

- · Designed and qualified according to JEDEC®-JESD 47
- Low IGT parts available
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





RoHS COMPLIANT **HALOGEN FREE**

APPLICATIONS

 Typical usage is in input rectification crowbar (soft start) and AC switch motor control, UPS, welding and battery charge

DESCRIPTION

The VS-40TPS... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

MAJOR RATINGS AND CHARACTERISTICS									
PARAMETER	TEST CONDITIONS	VALUES	UNITS						
I _{T(AV)}	Sinusoidal waveform	35	Α						
I _{RMS}		55	^						
V _{RRM} /V _{DRM}		800/1200	V						
I _{TSM}		600	А						
V _T	40 A, T _J = 25 °C	1.45	V						
dV/dt		1000	V/µs						
dl/dt		100	A/µs						
T _J		-40 to +125	°C						

VOLTAGE RATINGS									
PART NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} /I _{DRM} AT 125 °C mA						
VS-40TPS08APbF, VS-40TPS08A-M3	800	900							
VS-40TPS08PbF, VS-40TPS08-M3	800	900	10						
VS-40TPS12APbF, VS-40TPS12A-M3	1200	1300	10						
VS-40TPS12PbF, VS-40TPS12-M3	1200	1300							

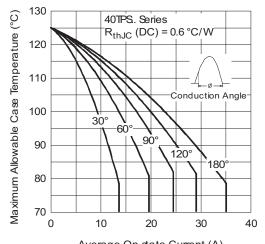


ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TE	EST CONDITIONS		VALUES	UNITS	
Maximum average on-state current	I _{T(AV)}	T _C = 79 °C, 180° cor	nduction half sine wave	e	35		
Maximum continuous RMS on-state current as AC switch	I _{T(RMS)}				55	А	
Maximum peak, one-cycle	I _{TSM}	10 ms sine pulse, rat	ted V _{RRM} applied		500		
non-repetitive surge current	TSM	10 ms sine pulse, no	latical	600			
Maximum I ² t for fusing	l ² t	10 ms sine pulse, rat	ted V _{RRM} applied	Initial $T_J = T_J \text{ max.}$	1250	A ² s	
Iviaximum i tior lusing	1 (10 ms sine pulse, no	voltage reapplied		1760	8	
Maximum I²√t for fusing	I ² √t	t = 0.1 ms to 10 ms,	17 600	A²√s			
Low level value of threshold voltage	V _{T(TO)1}		1.02	V			
High level value of threshold voltage	V _{T(TO)2}	T 105 00	1.23	\ \ \			
Low level value of on-state slope resistance	r _{t1}	T _J = 125 °C	9.74	0			
High level value of on-state slope resistance	r _{t2}				7.50	mΩ	
Maximum peak on-state voltage	V_{TM}	110 A, T _J = 25 °C			1.85	٧	
Maximum rate of rise of turned-on current	dI/dt	T _J = 25 °C			100	A/µs	
Maximum holding current	I _H	Anode supply = 6 V,	resistive load, initial T _J	= 1 A, I _T = 25 °C	200		
Maximum latching current	ΙL	Anode supply = 6 V,	resistive load, T _J = 25	°C	300		
Marian and a second all and the second		T _J = 25 °C	V Datady A		0.5	mA	
Maximum reverse and direct leakage current	I _{RRM/} I _{DRM}	T _J = 125 °C	$V_R = Rated V_{RRM}/V_{DRM}$		10		
Maximum rate of rise of off-state voltage 40TPS12A	d)//d+				500	V/µs	
Maximum rate of rise of off-state voltage 40TPS12	dV/dt	ij = ij maximum, iir	$T_J = T_J$ maximum, linear to 80 % V_{DRM} , R_g - k = 100 Ω				

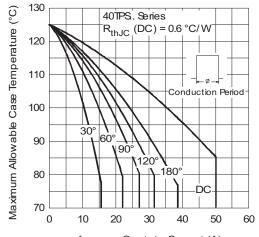
TRIGGERING					
PARAMETER	SYMBOL	TEST CO	NDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}			10	W
Maximum average gate power	P _{G(AV)}			2.5	VV
Maximum peak gate current	I _{GM}			2.5	Α
Maximum peak negative gate voltage	- V _{GM}			10	V
		T _J = - 40 °C		4.0	
Maximum required DC gate voltage to trigger	V_{GT}	T _J = 25 °C	Anode supply = 6 V	2.5	V
		T _J = 125 °C	- Tesistive load	1.7	
		T _J = - 40 °C		270	mA
Marian and ind DO and a small a literature		T _J = 25 °C	Anode supply = 6 V resistive load	150	
Maximum required DC gate current to trigger	I _{GT}	T _J = 125 °C	- Tesistive load	80	
		$T_J = 25$ °C, for 40TPS08AP	40		
Maximum DC gate voltage not to trigger for 40TPS12	V_{GD}	T 105 % V D-1-1		0.25	V
Maximum DC gate current not to trigger for 40TPS12	I _{GD}	$T_J = 125 ^{\circ}\text{C}, V_{DRM} = \text{Rated}$	6	mA	
Maximum DC gate voltage not to trigger for 40TPS12A	V_{GD}	T _ 125 °C V _ Dated	0.15	V	
Maximum DC gate current not to trigger for 40TPS12A	I _{GD}	$T_J = 125$ °C, $V_{DRM} = Rated$	value	1	mA

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THERMAL AND MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Maximum junction and storage temperature range	T_J , T_{Stg}		-40 to +125	°C					
Maximum thermal resistance, junction to case	R _{thJC}	DC eneration	0.6						
Maximum thermal resistance, junction to ambient	R _{thJA}	DC operation	40	°C/W					
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth and greased	0.2						
Approximate weight			6	g					
Approximate weight			0.21	OZ.					
Maurating torque			6 (5)	kgf · cm					
Mounting torque — maximum			12 (10)	(lbf \cdot in)					
			40TP:	S08A					
Madina davina		One of the TO 04740	40TP	S12A					
Marking device		Case style TO-247AC	40TPS08						
			40TPS12						



Average On-state Current (A)
Fig. 1 - Current Rating Characteristics



Average On-state Current (A)
Fig. 2 - Current Rating Characteristics

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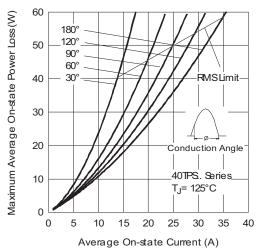
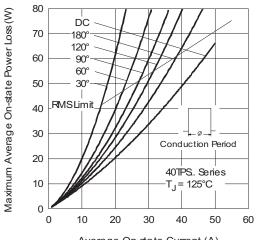


Fig. 3 - On-State Power Loss Characteristics



Average On-state Current (A)
Fig. 4 - On-State Power Loss Characteristics

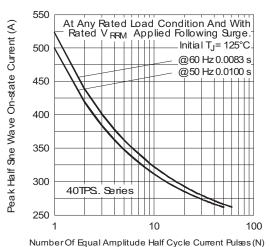


Fig. 5 - Maximum Non-Repetitive Surge Current

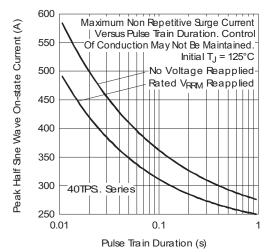


Fig. 6 - Maximum Non-Repetitive Surge Current

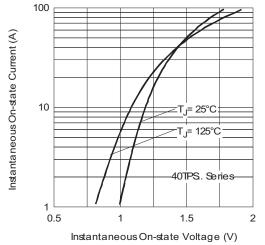


Fig. 7 - On-State Voltage Drop Characteristics

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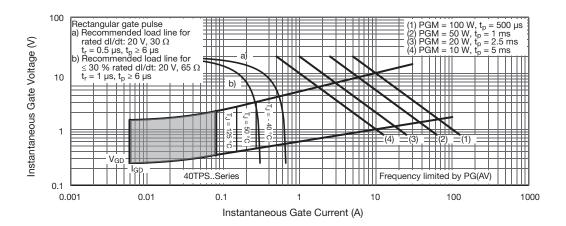


Fig. 8 - Gate Characteristics

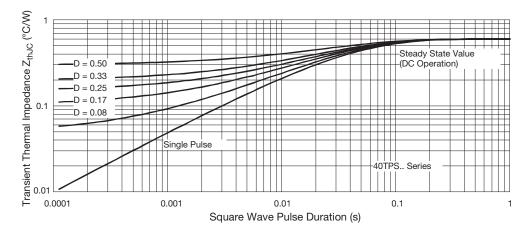
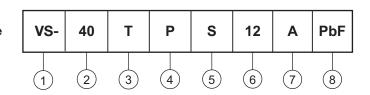


Fig. 9 - Thermal Impedance Z_{thJC} Characteristics

Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (40 = 40 A)

Circuit configuration:

T = Thyristor

4 - Package:

P = TO-247

5 - Type of silicon:

S = Standard recovery rectifier

08 = 800 V 12 = 1200 V

6 - Voltage ratings

• A = Low Igt selection 40 mA maximum

• None = Standard Igt selection

8 - Environmental digit:

PbF = Lead (Pb)-free and RoHS compliant

-M3 = Halogen-free, RoHS compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)										
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION							
VS-40TPS08APbF	25	500	Antistatic plastic tubes							
VS-40TPS08A-M3	25	500	Antistatic plastic tubes							
VS-40TPS08PbF	25	500	Antistatic plastic tubes							
VS-40TPS08-M3	25	500	Antistatic plastic tubes							
VS-40TPS12APbF	25	500	Antistatic plastic tubes							
VS-40TPS12A-M3	25	500	Antistatic plastic tubes							
VS-40TPS12PbF	25	500	Antistatic plastic tubes							
VS-40TPS12-M3	25	500	Antistatic plastic tubes							

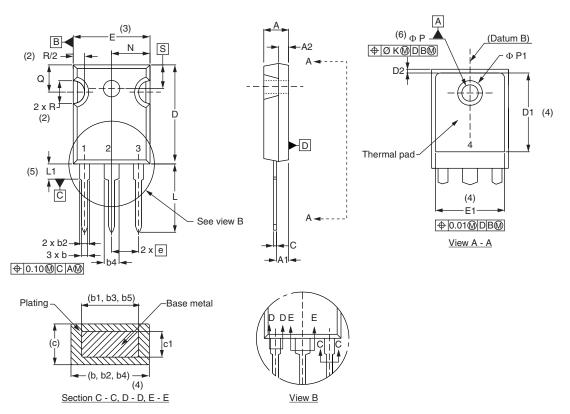
LINKS TO RELATED DOCUMENTS							
Dimensions		www.vishay.com/doc?95542					
Part marking information	TO-247AC PbF	www.vishay.com/doc?95226					
	TO-247AC-M3	www.vishay.com/doc?95007					



Vishay Semiconductors

TO-247

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	MILLIMETERS		INCHES			SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.65	5.31	0.183	0.209			D2	0.51	1.30	0.020	0.051	
A1	2.21	2.59	0.087	0.102			Е	15.29	15.87	0.602	0.625	3
A2	1.50	2.49	0.059	0.098			E1	13.72	-	0.540	-	
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	BSC	
b1	0.99	1.35	0.039	0.053			ØΚ	2.	54	0.0)10	
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634	
b3	1.65	2.34	0.065	0.092			L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135			Ν	7.62 BSC		0	.3	
b5	2.59	3.38	0.102	0.133			ØΡ	3.56	3.66	0.14	0.144	
С	0.38	0.89	0.015	0.035			Ø P1	-	6.98	-	0.275	
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	BSC	

Notes

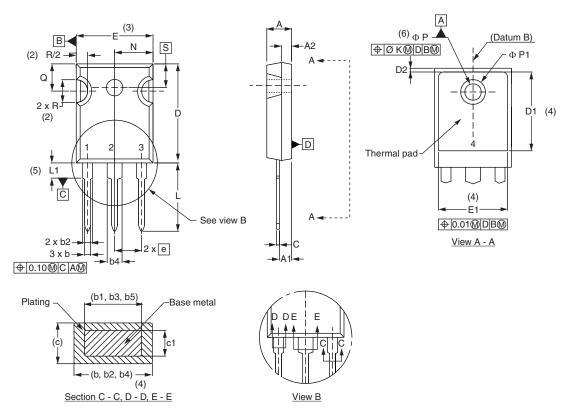
- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- $^{(7)}\,$ Outline conforms to JEDEC® outline TO-247 with exception of dimension c



Vishay Semiconductors

TO-247 - 50 mils L/F

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS	IETERS	INC	HES	NOTES		SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.65	5.31	0.183	0.209			D2	0.51	1.35	0.020	0.053	
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.625	3
A2	1.17	1.37	0.046	0.054			E1	13.46	=.	0.53	-	
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	BSC	
b1	0.99	1.35	0.039	0.053			ØK	0.2	254	0.0	10	
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634	
b3	1.65	2.34	0.065	0.092			L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135			N	7.62	BSC	0	.3	
b5	2.59	3.38	0.102	0.133			ØΡ	3.56	3.66	0.14	0.144	
С	0.38	0.89	0.015	0.035			Ø P1	ı	7.39	-	0.291	
c1	0.38	0.84	0.015	0.033			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3		R	4.52	5.49	0.178	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	BSC	

Notes

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Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

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